

ABSTRACT OF THE DISCLOSURE

A method of annealing a metal layer on a substrate in a chamber is provided. The method comprises positioning a substrate with a metal layer thereon in a chamber, removing atmospheric gases from the chamber, providing process gas to the chamber, and annealing the metal layer at a temperature greater than about 80 degrees Celsius. Also provided is a method of forming a feature on a substrate. The method comprises depositing a dielectric layer on the substrate, forming at least one opening within the dielectric layer, depositing a metal layer in the opening, positioning the substrate in an annealing chamber, removing atmospheric gases from the annealing chamber, providing process gas to the annealing chamber, and annealing the metal layer at temperature greater than about 80 degrees Celsius.